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Degradation of quantum dot light emitting diodes, the case under low driving level

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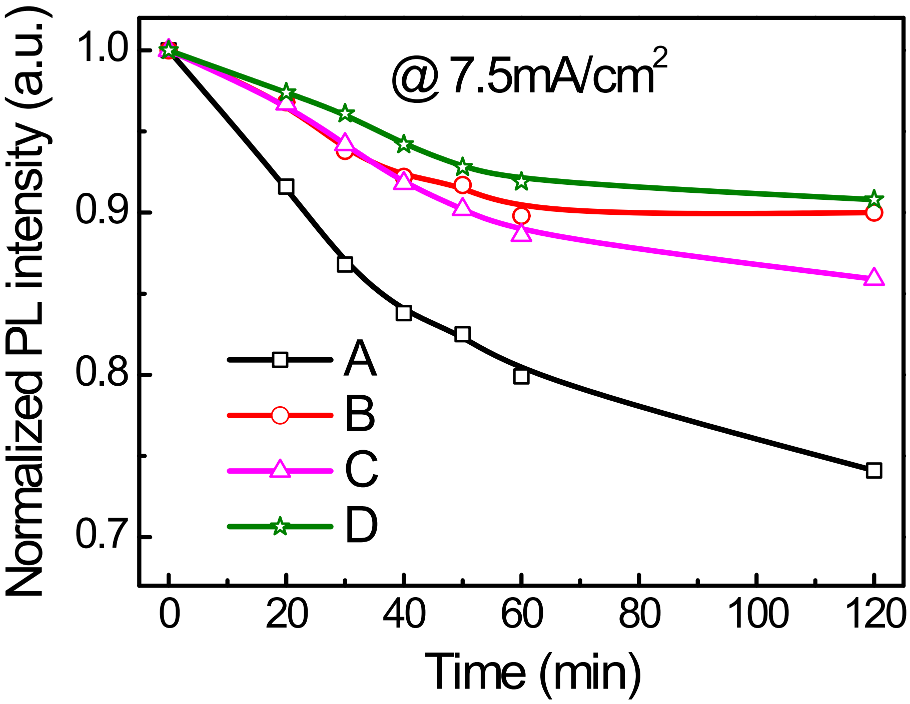

Figure S1 Evolution of PL intensities as the function of aging time for different devices.

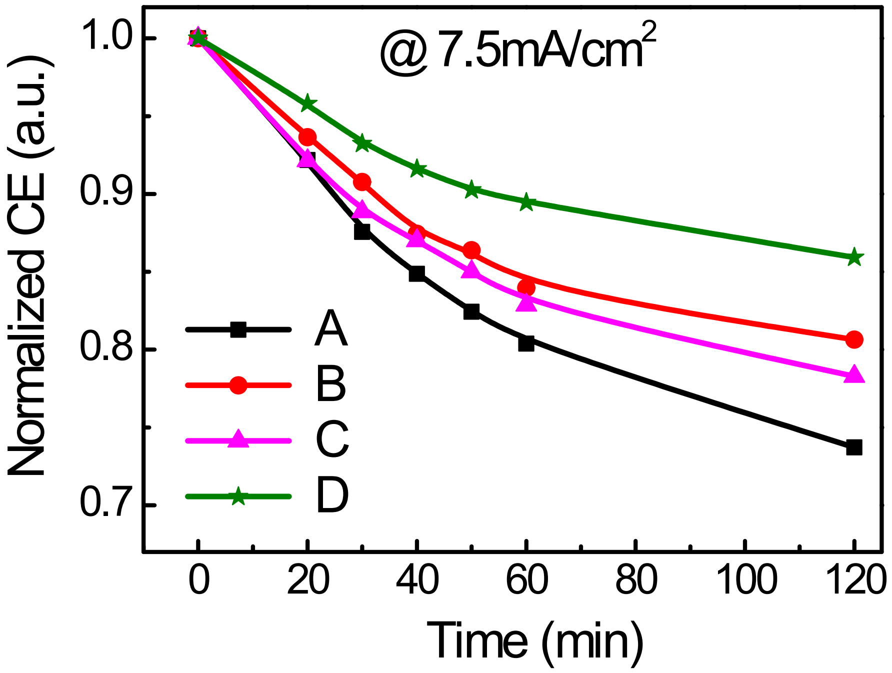

Figure S2 Changes of the current efficiencies (CE) for different devices with the aging time.

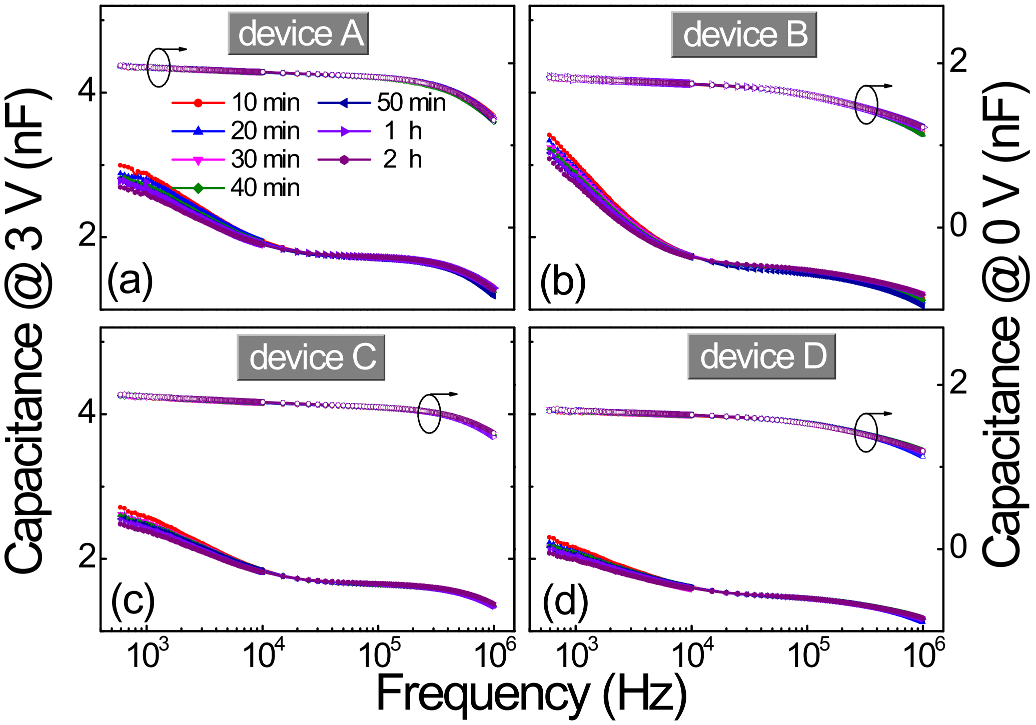

Figure S3. Capacitance-frequency properties of four QLED devices driven at 7.5 mA/cm2 for different aging times.

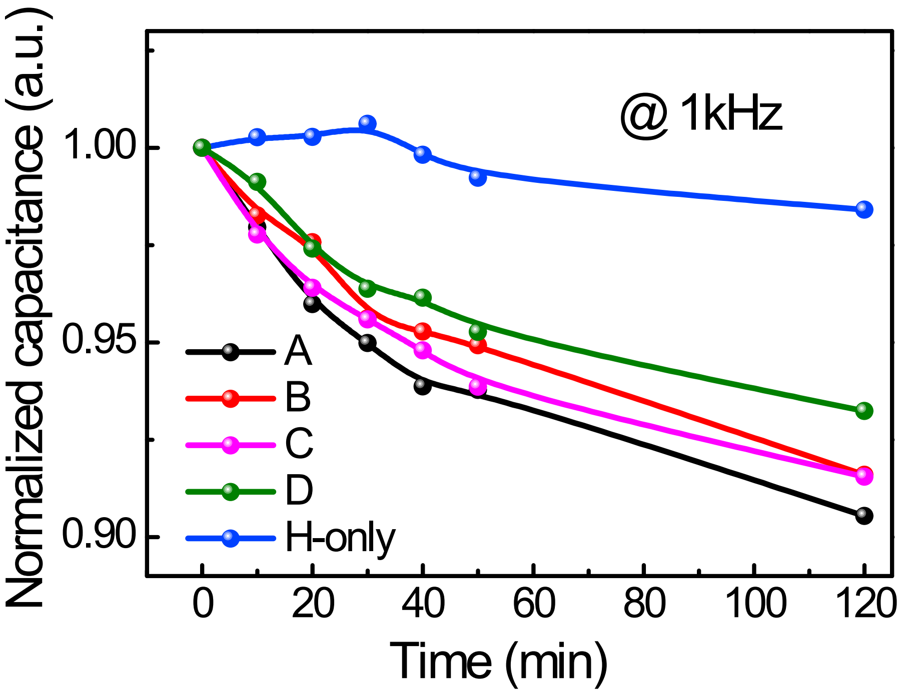

Figure S4. Normalized capacitances of the QLED devices and the ETL-free device with the aging time at applied voltage of 3 V and 1 kHz. The ETL-free device consists of ITO/QDs(~25 nm)/TCTA (65 nm)/MoO_3 (8 nm)/Al (100 nm).